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Amendments to the Abstract:**Please amend the abstract as follows:****Abstract**

B17

On a substrate made of e.g., sapphire single crystal is formed an Al underlayer having a crystallinity FWHM X-ray rocking curve value of 90 seconds or below in FWHM of X-ray rocking curve. Then, ~~on the AlN underlayer is formed a~~ buffer layer is formed on the AlN underlayer and has having a composition of $\text{Al}_p\text{Ga}_q\text{In}_{1-p-q}\text{N}$ ($0 \leq p \leq 1$, $0 \leq q \leq 1$), ~~and a GaN-based semiconductor layer group is formed on the buffer layer, is formed a GaN-based semiconductor layer group:~~